P -CHANNEL ENHANCEMENT MODE POWER MOSFET

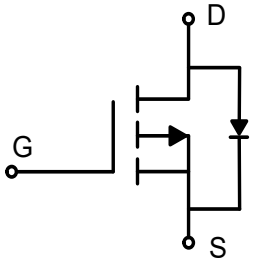
TF800P10K

Description

TF800P10K uses advanced power trench technology that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Features

- V_{DS} = -100V , I_D = -18A
  $R_{DS(on)}$ < 95mΩ @ V_{GS} = -10V
  $R_{DS(on)}$ < 105mΩ @ V_{GS} = -4.5V
- Extremely Low Switching Loss
- Excellent Stability and Uniformity
- Low Gate Charge
- 100% EAS Guaranteed



Applications

- Power Management Switches
- DC/DC Converter

Absolute Maximum Ratings (T_A = 25°C, unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	-100	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C= 25°C	I_D	-18	A
	T_C= 100°C		-11	
Pulsed Drain Current[1]		I_{DM}	-72	A
Single Pulse Avalanche Energy[2]		EAS	132.25	mJ
Total Power Dissipation	T_C= 25°C	P_D	70	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient[3]	$R_{\theta JA}$	75	°C/W
Thermal Resistance from Junction-to-Case	$R_{\theta JC}$	1.78	°C/W

Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-100	-	-	V
Gate-body Leakage current		I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T_J= 25°C	I_{DSS}	V_{DS} = -100V, V_{GS} = 0V	-	-	-1	μA
	T_J= 100°C			-	-	-100	
Gate-Threshold Voltage		$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-1	-1.8	-2.5	V
Drain-Source On-Resistance[4]		$R_{DS(on)}$	V_{GS} = -10V, I_D = -10A	-	83	95	mΩ
			V_{GS} = -4.5V, I_D = -7A		88	105	
Forward Transconductance[4]		g_{fs}	V_{DS} = -10V, I_D = -10A	-	30	-	S
Dynamic Characteristics[5]							
Input Capacitance		C_{iss}	V_{DS} = -50V, V_{GS} = 0V, f = 1MHz	-	3985	-	pF
Output Capacitance		C_{oss}		-	85	-	
Reverse Transfer Capacitance		C_{rss}		-	71	-	
Gate Resistance		R_g	f = 1MHz	-	4	-	Ω
Switching Characteristics[5]							
Total Gate Charge		Q_g	V_{GS} = -10V, V_{DS} = -50V, I_D= -10A	-	65	-	nC
Gate-Source Charge		Q_{gs}		-	10.2	-	
Gate-Drain Charge		Q_{gd}		-	13	-	
Turn-On Delay Time		$t_{d(on)}$	V_{GS} = -10V, V_{DD} = -50V, R_G = 3Ω, I_D= -10A	-	12.8	-	ns
Rise Time		t_r		-	30	-	
Turn-Off Delay Time		$t_{d(off)}$		-	82	-	
Fall Time		t_f		-	61	-	
Body Diode Reverse Recovery Time		t_{rr}	I_F = -10A,dI/dt= 100A/μs	-	62	-	ns
Body Diode Reverse Recovery Charge		Q_{rr}		-	56	-	nC
Drain-Source Body Diode Characteristics							
Diode Forward Voltage[4]		V_{SD}	I_S = -10A, V_{GS} = 0V	-	-	-1.2	V
Continuous Source Current	T_C= 25°C	I_S	-	-	-	-18	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C.
2. The EAS data shows Max. rating . The test condition is V_{DD}= -35V, V_{GS}= -10V, L= 0.5mH, I_{AS}= -23A
3. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test..

Typical Characteristics

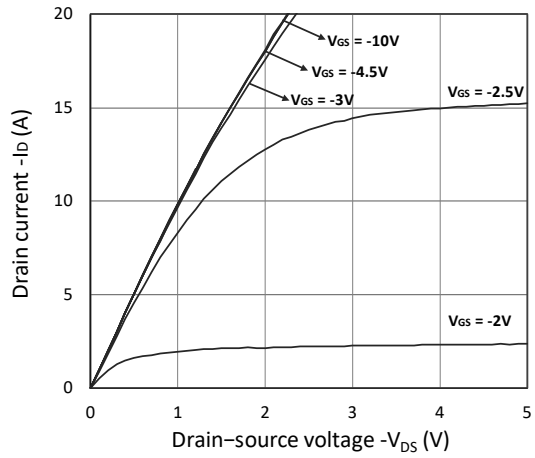


Figure 1. Output Characteristics

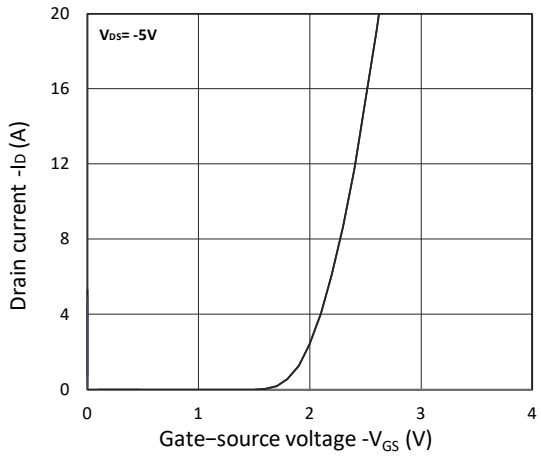


Figure 2. Transfer Characteristics

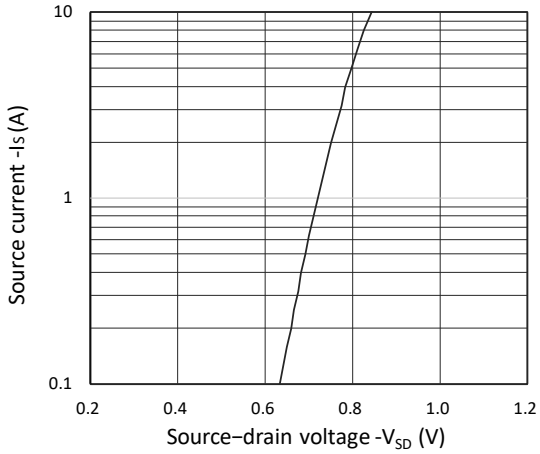


Figure 3. Forward Characteristics of Reverse

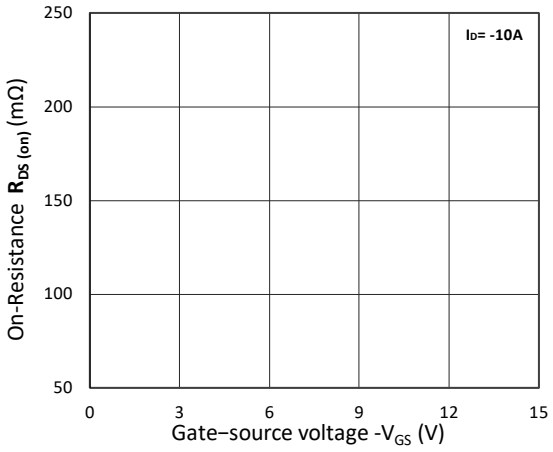


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

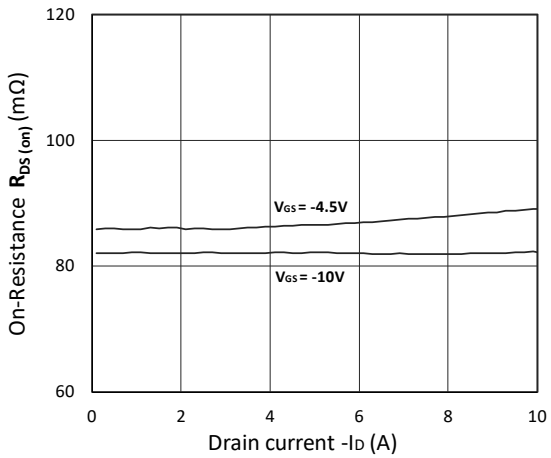


Figure 5. $R_{DS(ON)}$ vs. I_D

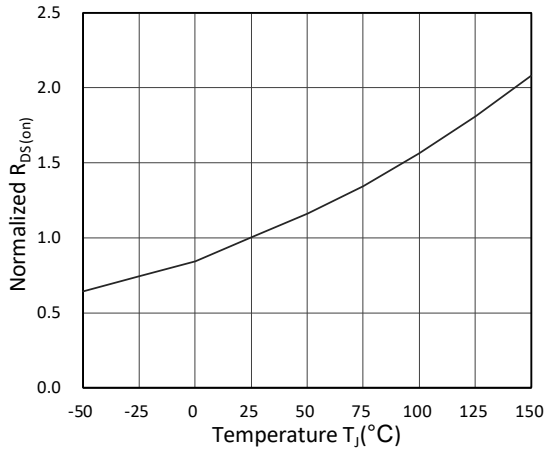


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

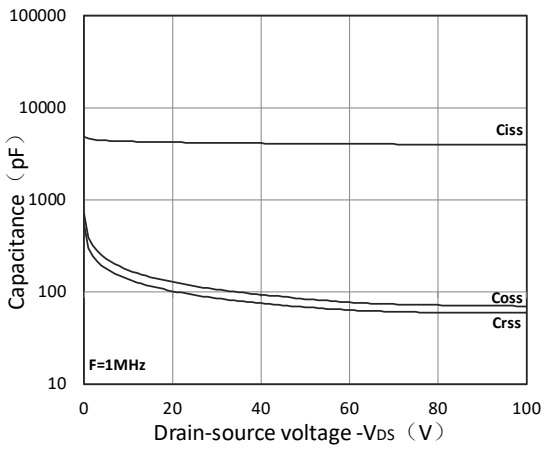


Figure 7. Capacitance Characteristics

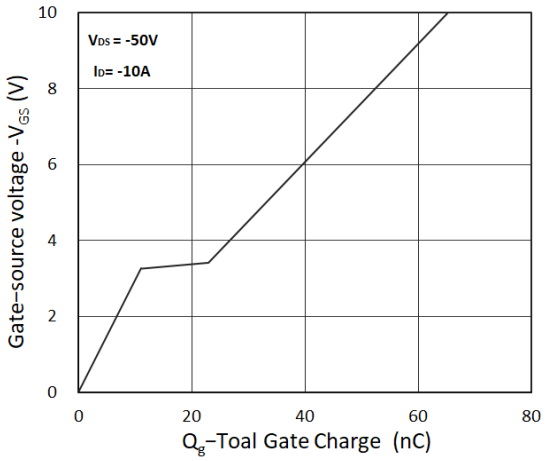


Figure 8. Gate Charge Characteristics

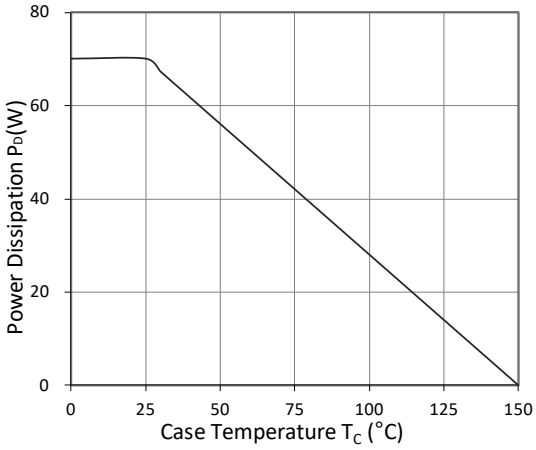


Figure 9. Power Dissipation

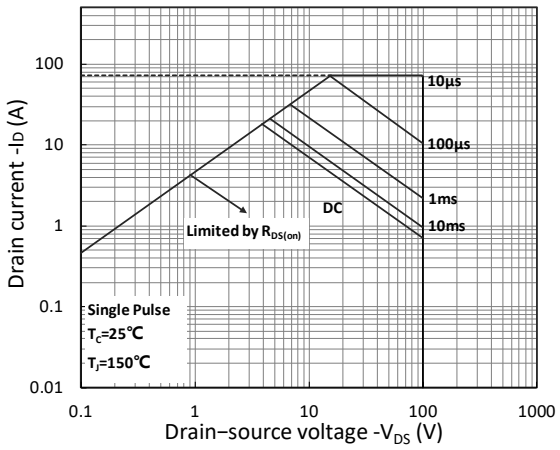


Figure10. Safe Operating Area

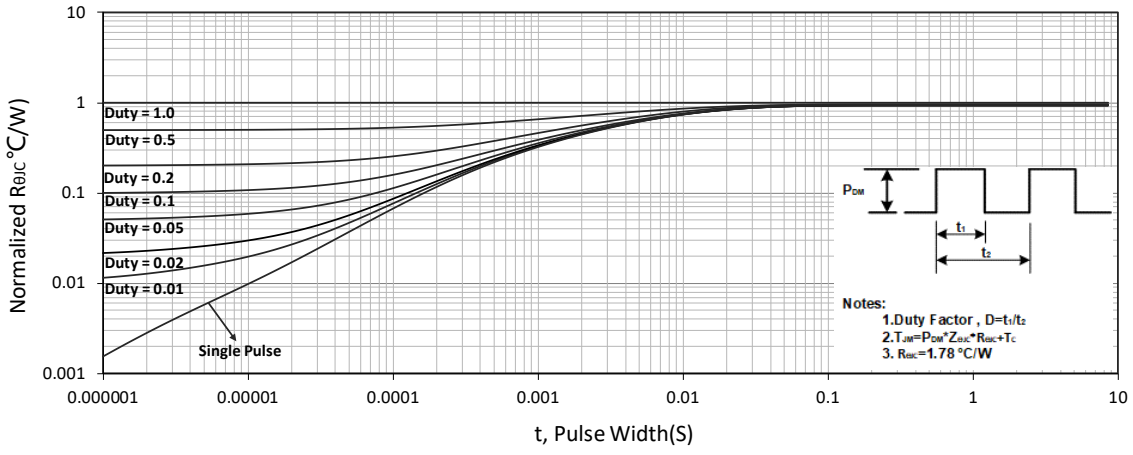


Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

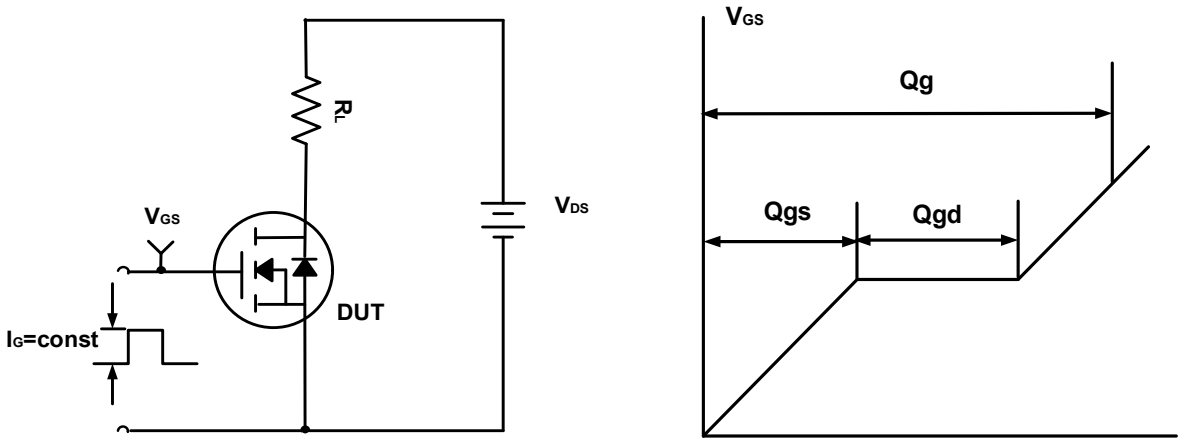


Figure A. Gate Charge Test Circuit & Waveforms

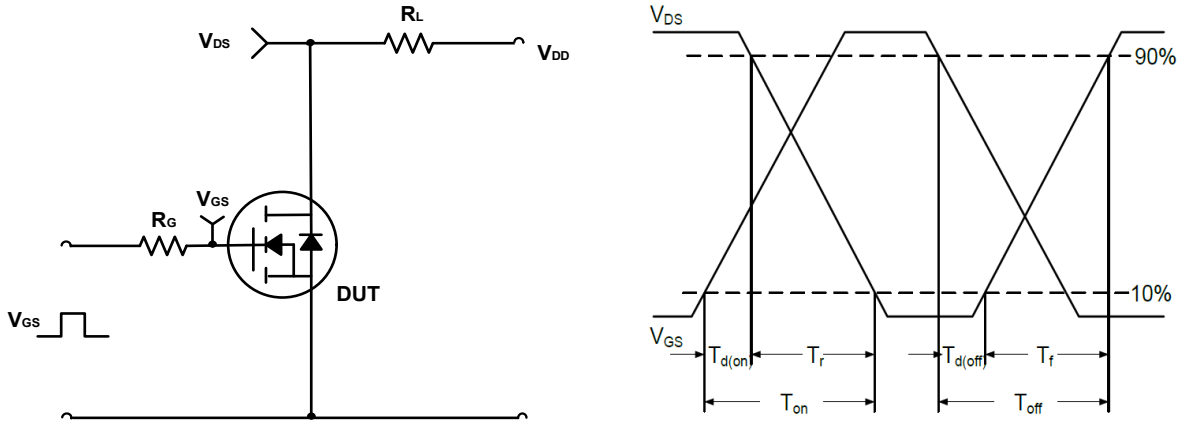


Figure B. Switching Test Circuit & Waveforms

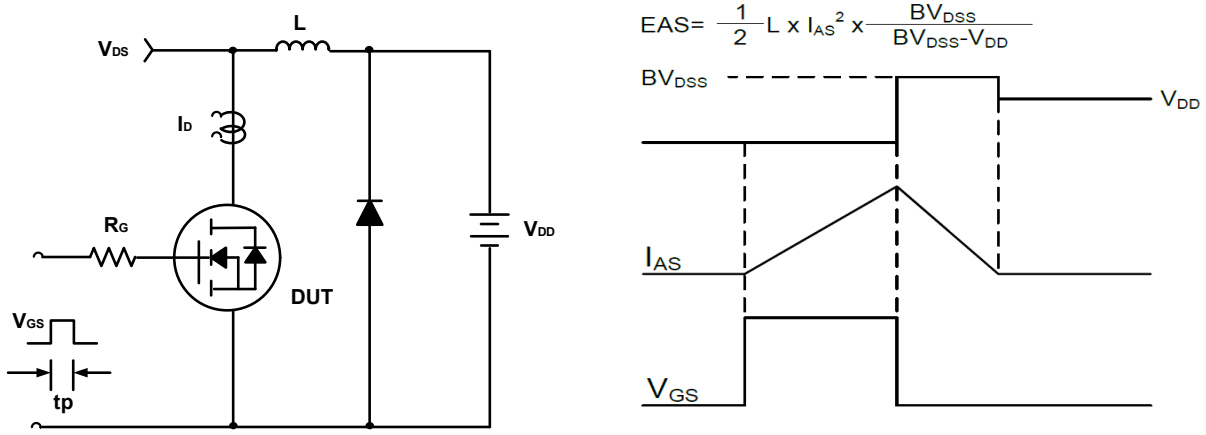
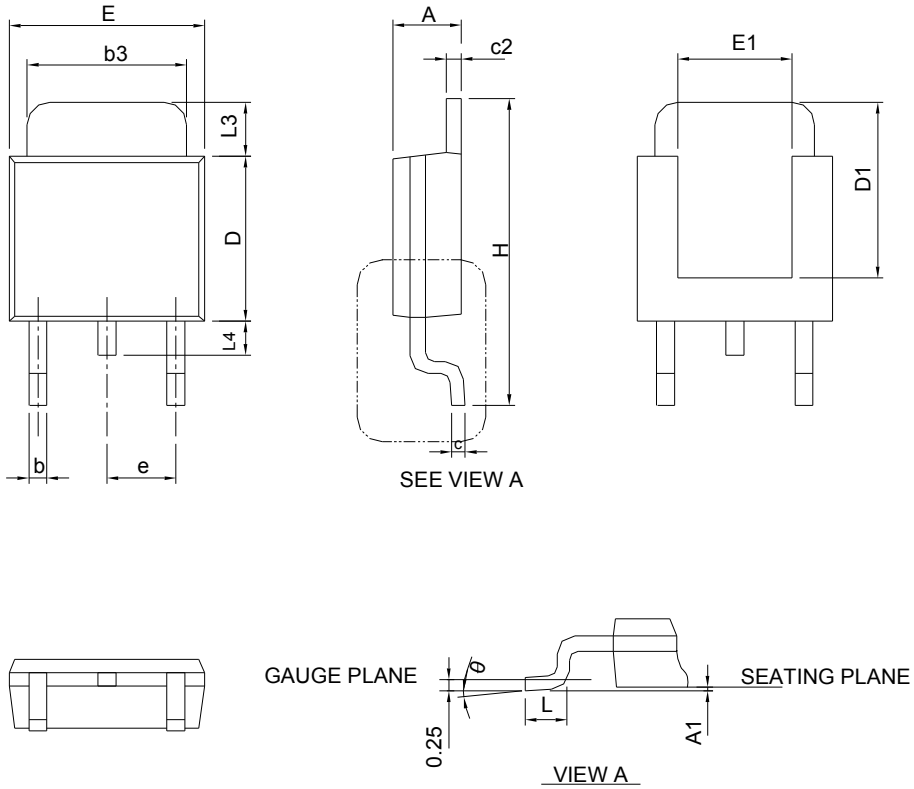


Figure C. Unclamped Inductive Switching Circuit & Waveforms

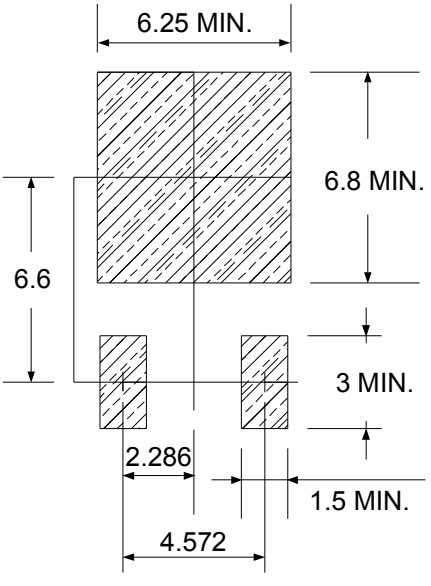
Package Information

TO-252



SYMBOL	TO-252			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1		0.13		0.005
b	0.50	0.89	0.020	0.035
b3	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.33	6.22	0.210	0.245
D1	4.57	6.00	0.180	0.236
E	6.35	6.73	0.250	0.265
E1	3.81	6.00	0.150	0.236
e	2.29 BSC		0.090 BSC	
H	9.40	10.41	0.370	0.410
L	0.90	1.78	0.035	0.070
L3	0.89	2.03	0.035	0.080
L4		1.02		0.040
θ	0°	8°	0°	8°

RECOMMENDED LAND PATTERN



UNIT: mm